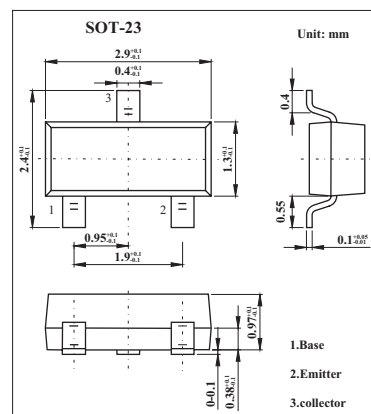


Power Transistor

2SD2444K

■ Features

- $I_c = 1A$.
- Low saturation voltage.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	15	V
Collector-emitter voltage	V_{CEO}	15	V
Emitter-base voltage	V_{EB0}	6	V
Collector current	I_c	1	A
Collector power dissipation	P_c	0.2	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* Single pulse $P_w=100ms$.

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CB0}	$I_c=50\mu A$	15			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_c=1mA$	15			V
Emitter-base breakdown voltage	BV_{EB0}	$I_E=50\mu A$	6			V
Collector cutoff current	I_{CBO}	$V_{CB}=12V$			0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=5V$			0.5	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c/I_B=400mA/20mA$			0.3	V
DC current transfer ratio	h_{FE}	$V_{CE}=2V, I_c=50mA$	180		390	
Output capacitance	f_T	$V_{CE}=2V, I_E=-50mA, f=100MHz$		200		MHz
Transition frequency	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		15		pF

■ h_{FE} Classification

Marking	BSR
h_{FE}	180~390